| Notice of References Cited | Application/Control No. 10/677,614 | Applicant(s)/Patent Under Reexamination CHAKRAVARTHI ET AL. | |
|---|---|---|---|
| | Examiner Jennifer M. Dolan | Art Unit 2813 | Page 1 of 1 |

**U.S. PATENT DOCUMENTS**

| * | | Document Number Country Code-Number-Kind Code | Date MM-YYYY | Name | Classification |
|---|---|---|---|---|---|
| * | A | US-6,812,523 | 11-2004 | Chu et al. | 257/335 |
| * | B | US-5,976,939 | 11-1999 | Thompson et al. | 438/305 |
| * | C | US-6,069,062 | 05-2000 | Downey, Daniel F. | 438/528 |
| * | D | US-2001/0041432 | 11-2001 | Lee, Kam Leung | 438/530 |
| * | E | US-6,153,920 | 11-2000 | Gossmann et al. | 257/607 |
| * | F | US-5,994,175 | 11-1999 | Gardner et al. | 438/199 |
| | G | US- | | | |
| | H | US- | | | |
| | I | US- | | | |
| | J | US- | | | |
| | K | US- | | | |
| | L | US- | | | |
| | M | US- | | | |

**FOREIGN PATENT DOCUMENTS**

| * | | Document Number Country Code-Number-Kind Code | Date MM-YYYY | Country | Name | Classification |
|---|---|---|---|---|---|---|
| | N | | | | | |
| | O | | | | | |
| | P | | | | | |
| | Q | | | | | |
| | R | | | | | |
| | S | | | | | |
| | T | | | | | |

**NON-PATENT DOCUMENTS**

| * | | Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages) |
|---|---|---|
| | U | S. Saito, "Defect reduction by MeV ion implantation for shallow junction formation," Appl. Phys. Lett. vol 63, No. 2, pp 197-199. 12 July 1993. |
| | V | T.H. Huang et al., "Influence of fluorine preamorphization on the diffusion and activation of low-energy implanted boron during rapid thermal annealing," Appl. Phys. Lett. vol 65, no. 14, pp 1829-1831. 3 October 1994. |
| | W | |
| | X | |

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.